

2N3905



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 100 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N3905	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

PNP General Purpose Amplifier (continued)

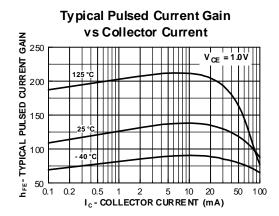
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF OLIA	DAOTEDIOTIOO				
	RACTERISTICS	1 40 1 0	1 40	1	1 1/
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	5.0		V
I _{CEX}	Collector Cutoff Current	$V_{CE} = 30 \text{ V}, V_{OB} = 3.0 \text{ V}$		50	nA
BL	Base Cutoff Current	$V_{CE} = 30 \text{ V}, V_{OB} = 3.0 \text{ V}$		50	nA
ON CHAR	ACTERISTICS*				
h _{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 0.1 \text{ mA}$	30		1
' 'FE	Do current Gam	$V_{CE} = 1.0 \text{ V}, I_{C} = 0.1 \text{ Hz}$	40		
		$V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	50	150	
		$V_{CE} = 1.0 \text{ V}, I_{C} = 50 \text{ mA}$	30		
\ /	Collector-Emitter Saturation Voltage	$V_{CE} = 1.0 \text{ V}, I_{C} = 100 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$	15	0.25	V
$V_{CE(sat)}$	Collector-Enritter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.23	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10 mA, I _B = 1.0 mA	0.65	0.85	V
V _{BE(sat)}	Base-Emitter Saturation Voltage		0.65	0.85 0.95	V V
SMALL S	IGNAL CHARACTERISTICS	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	0.65	0.95	V
SMALL S	IGNAL CHARACTERISTICS Output Capacitance	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	0.65	0.95	V V pF
SMALL S	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$		0.95	V
SMALL S	IGNAL CHARACTERISTICS Output Capacitance	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	2.0	0.95	pF
SMALL S C _{ob} C _{ib}	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$ $I_{C} = 10 \text{ mA}, V_{CE} = 20 \text{ V},$		0.95	pF
SMALL S Cob Cib hfe	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \end{split}$	2.0	0.95 4.5 10	pF
SMALL S C _{ob} C _{ib} Drie	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \end{split}$	2.0	0.95 4.5 10	pF pF
SMALL S Cob Cib hre hre hie	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \end{split}$	2.0 50 0.1	0.95 4.5 10 200 5.0	PF PF x10 ⁻⁴ kΩ
SMALL S Cob Cib hre	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ \end{split} $V_{CE} &= 5.0 \text{ V, } I_C = 100 \mu\text{A, } \\ R_S &= 1.0 k\Omega, \end{split}$	2.0 50 0.1 0.5	0.95 4.5 10 200 5.0 8.0	PF PF x10 ⁻⁴ kΩ
SMALL S Cob Cib hre hre hre hie hoe	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ \end{split} $V_{CE} = 5.0 \text{ V, } I_C = 100 \mu\text{A, } \\ V_{CE} = 5.0 \text{ V, } I_C = 100 \mu\text{A, } \end{split}$	2.0 50 0.1 0.5	0.95 4.5 10 200 5.0 8.0 40	PF PF x10 ⁻⁴ kΩ μmhos
SMALL S Cob Cib Ofe Ofe One	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance Noise Figure	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ \end{split} $V_{CE} &= 5.0 \text{ V, } I_C = 100 \mu\text{A, } \\ R_S &= 1.0 k\Omega, \end{split}$	2.0 50 0.1 0.5	0.95 4.5 10 200 5.0 8.0 40	PF PF x10 ⁻⁴ kΩ μmhos
SMALL S Cob Cib Ofe Ofe Noe NF	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance Noise Figure NG CHARACTERISTICS	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ \end{split} $V_{CE} &= 5.0 \text{ V, } I_C = 100 \mu\text{A, } \\ R_S &= 1.0 k\Omega, \\ B_W &= 10 \text{ Hz to } 15.7 \text{ KHz} \end{split}$	2.0 50 0.1 0.5	0.95 4.5 10 200 5.0 8.0 40 5.0	PF PF x10 ⁻⁴ kΩ μmhos dB
SMALL S Cob Cib Ofe Ore Ooe NF	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance Noise Figure NG CHARACTERISTICS Delay Time	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ \end{split}$ $\begin{split} I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $\begin{split} I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ $\begin{split} V_{CE} &= 5.0 \text{ V, } I_C = 100 \mu\text{A, } \\ R_S &= 1.0 k\Omega, \\ R_W &= 10 \text{ Hz to } 15.7 \text{ KHz} \\ \end{split}$ \end{split} $V_{CC} &= 3.0 \text{ V, } I_{CS} = 10 \text{ mA, } \end{split}$	2.0 50 0.1 0.5	0.95 4.5 10 200 5.0 8.0 40 5.0	PF PF x10 ⁻⁴ kΩ μmhos dB

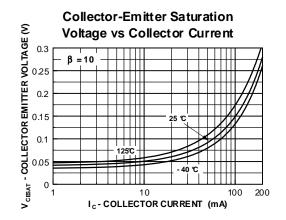
^{*}Pulse Test: Pulse Width ≤300 μs, Duty Cycle ≤2.0%

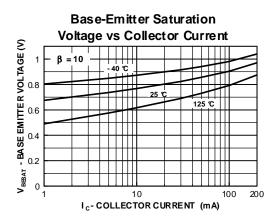
PNP General Purpose Amplifier

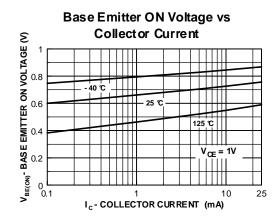
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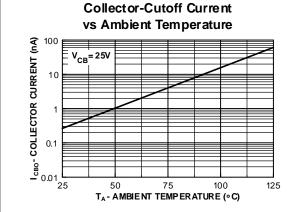
Typical Characteristics

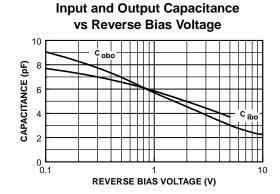










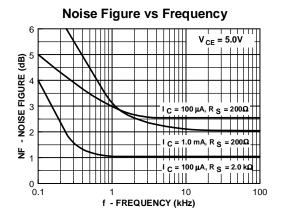


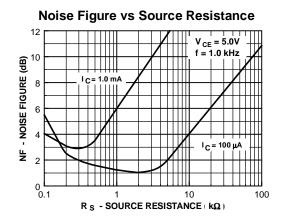
Common-Base Open Circuit

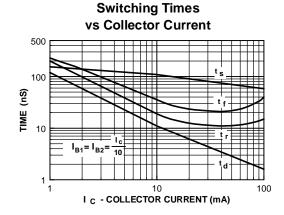
PNP General Purpose Amplifier

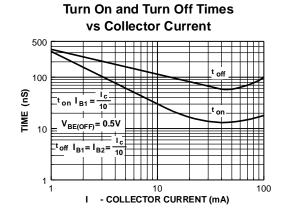
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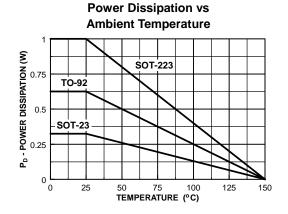
Typical Characteristics (continued)







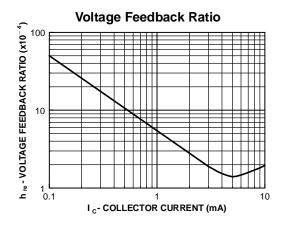


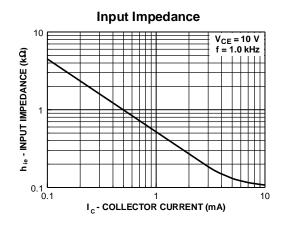


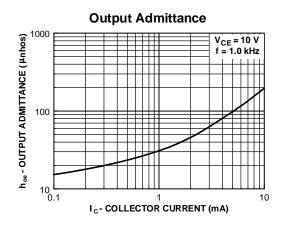
PNP General Purpose Amplifier

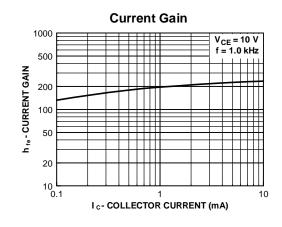
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Typical Characteristics (continued)









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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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